

N-Channel JFETs

Product Summary

Part Number	V _{GS(off)} (V)	V _{(BR)GSS} Min (V)	g _{fs} Min (mS)	I _{DSS} Min (mA)
J304	-2 to -6	-30	4.5	5
J305	-0.5 to -3	-30	3	1

Features

- Excellent High Frequency Gain: J304, Gps 11 dB (typ) @ 400 MHz
- Very Low Noise: 3.8 dB (typ) @ 400 MHz
- Very Low Distortion
- High ac/dc Switch Off-Isolation
- High Gain: A_V = 60 @ 100 μ A

Benefits

- Wideband High Gain
- Very High System Sensitivity
- High Quality of Amplification
- High-Speed Switching Capability
- High Low-Level Signal Amplification

Applications

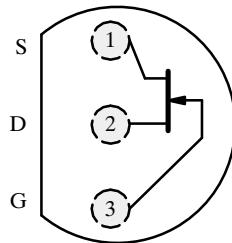
- High-Frequency Amplifier/Mixer
- Oscillator
- Sample-and-Hold
- Very Low Capacitance Switches

Description

The J304/305 n-channel JFETs provide high-performance amplification, especially at high-frequency. These products are available in tape and reel for automated assembly (see Package Information).

For similar products in TO-236 (SOT-23) packages, see the 2N/SST5484 series data sheet, or in TO-206AF (TO-72) packages, see the 2N/SST4416 series data sheet.

TO-226AA
(TO-92)



Top View

Absolute Maximum Ratings

Gate-Source/Gate-Drain Voltage	-30 V
Forward Gate Current	10 mA
Storage Temperature	-55 to 150°C
Operating Junction Temperature	-55 to 150°C

Lead Temperature (1/16" from case for 10 sec.)	300°C
Power Dissipation ^a	350 mW

Notes

a. Derate 2.8 mW/°C above 25°C

J304/305

TEMIC

Siliconix

Specifications^a

Parameter	Symbol	Test Conditions	Typ ^b	Limits				Unit	
				J304		J305			
				Min	Max	Min	Max		
Static									
Gate-Source Breakdown Voltage	V _{(BR)GSS}	I _G = -1 μA, V _{DS} = 0 V	-35	-30		-30		V	
Gate-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = 15 V, I _D = 1 nA		-2	-6	-0.5	-3		
Saturation Drain Current ^c	I _{DSS}	V _{DS} = 15 V, V _{GS} = 0 V		5	15	1	8	mA	
Gate Reverse Current	I _{GSS}	V _{GS} = -20 V, V _{DS} = 0 V	-2	T _A = 100°C	-100		-100	pA	
Gate Operating Current ^c	I _G	V _{DG} = 10 V, I _D = 1 mA	-20					pA	
Drain Cutoff Current	I _{D(off)}	V _{DS} = 10 V, V _{GS} = -6 V	2						
Drain-Source On-Resistance	r _{DS(on)}	V _{GS} = 0 V, I _D = 1 mA	200					Ω	
Gate-Source Forward Voltage	V _{GS(F)}	I _G = 1 mA, V _{DS} = 0 V	0.7					V	
Dynamic									
Common-Source Forward Transconductance	g _{fs}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 kHz		4.5	7.5	3		mS	
Common-Source Output Conductance	g _{os}				50		50	μS	
Common-Source Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V f = 1 MHz	2.2					pF	
Common-Source Reverse Transfer Capacitance	C _{rss}		0.7						
Common-Source Output Capacitance	C _{oss}		1						
Equivalent Input Noise Voltage	ē _n	V _{DS} = 10 V, V _{GS} = 0 V f = 100 Hz	10					nV/√Hz	

Typical High-Frequency Specifications^a

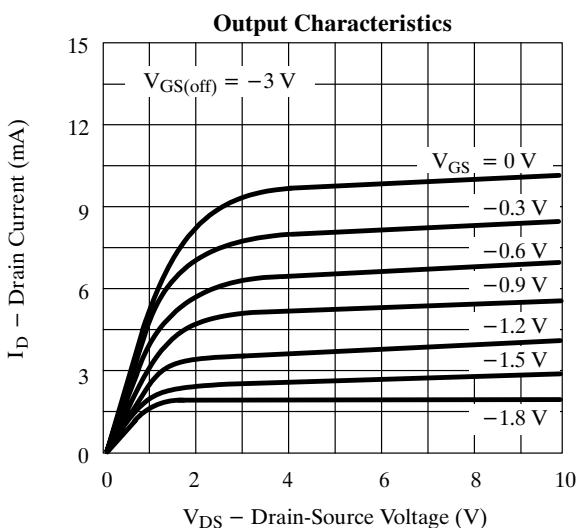
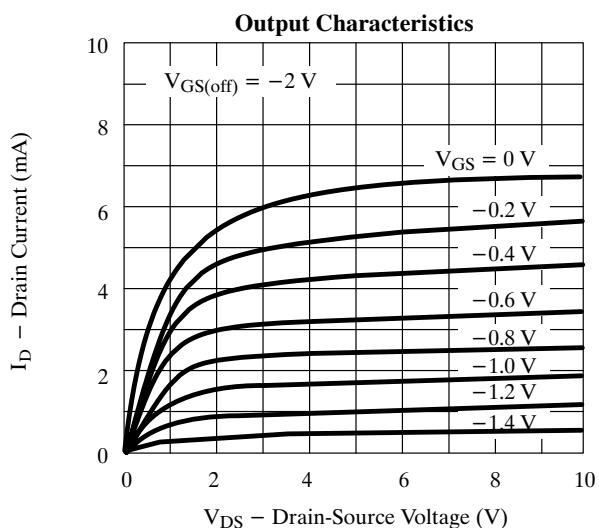
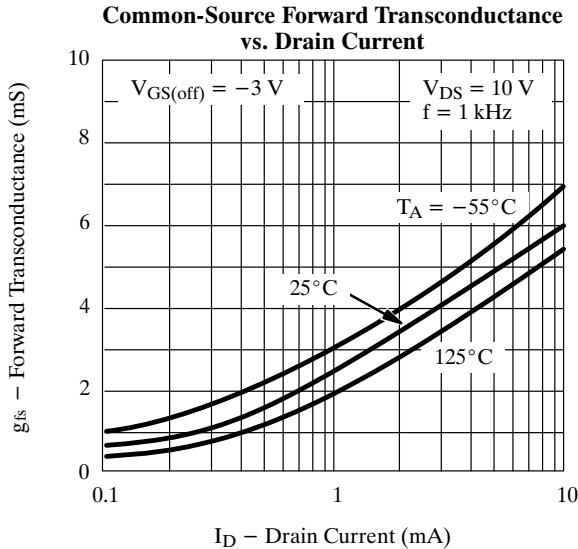
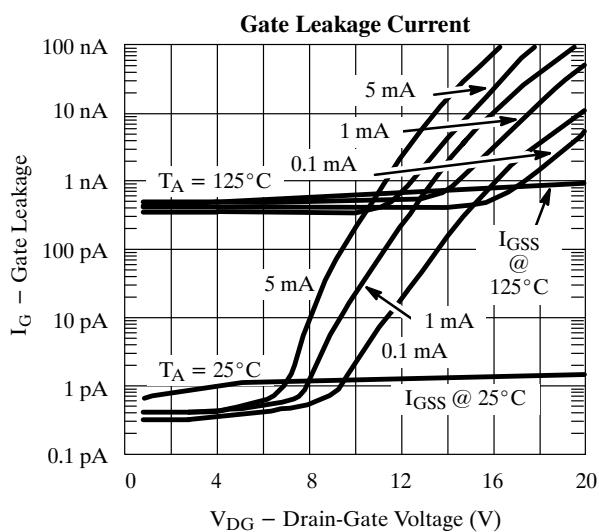
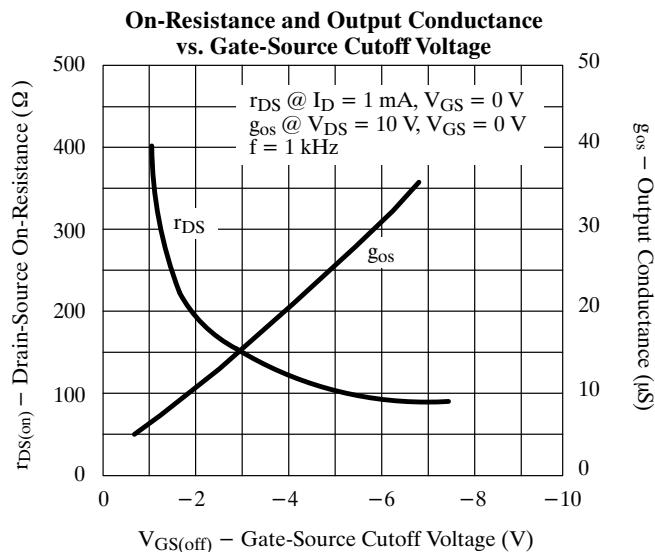
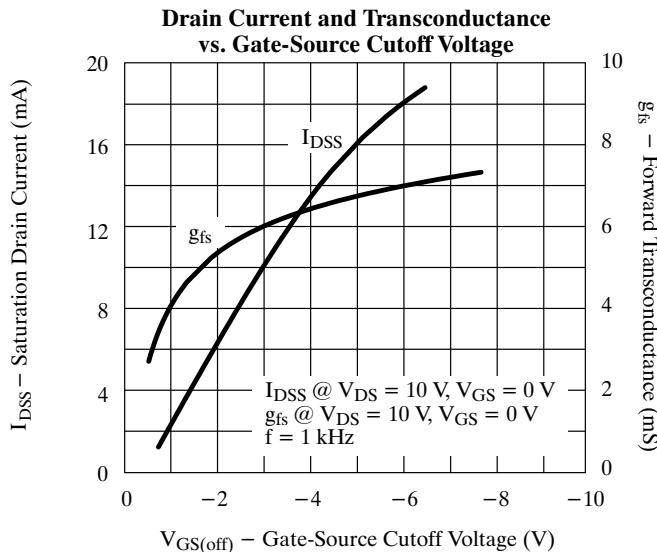
Parameter	Symbol	Test Conditions	Limits (Typ)				Unit	
			J304		J305			
			100 MHz	400 MHz	100 MHz	400 MHz		
High-Frequency								
Common-Source Input Conductance	g _{iss}	V _{DS} = 15 V, V _{GS} = 0 V	80	800	80		μS	
Common-Source Input Susceptance	b _{iss}		2	7.5	2			
Common-Source Output Conductance	g _{oss}		60	80	60		μS	
Common-Source Output Susceptance	b _{oss}		0.8	3.6	0.8			
Common-Source Forward Transconductance	g _{fs}		4.4	4.2	3		mS	
Common-Source Power Gain	G _{ps}		20	11				
Noise Figure	NF	V _{DS} = 15 V, I _D = 5 mA R _G = 1 kΩ	1.7	3.8			dB	

Notes

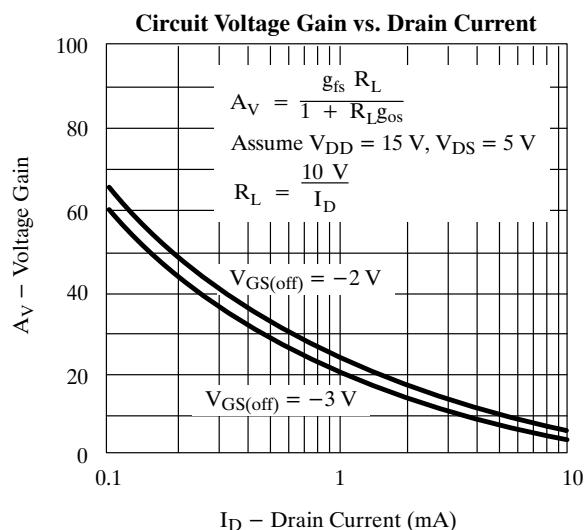
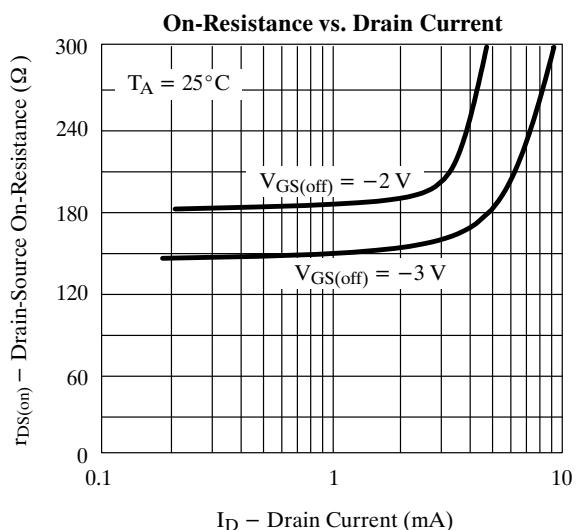
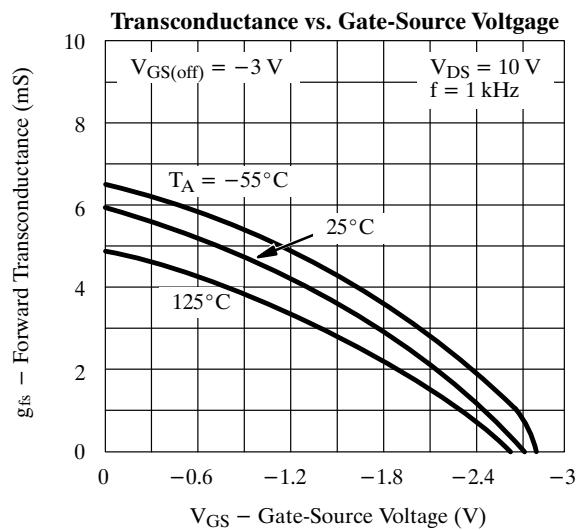
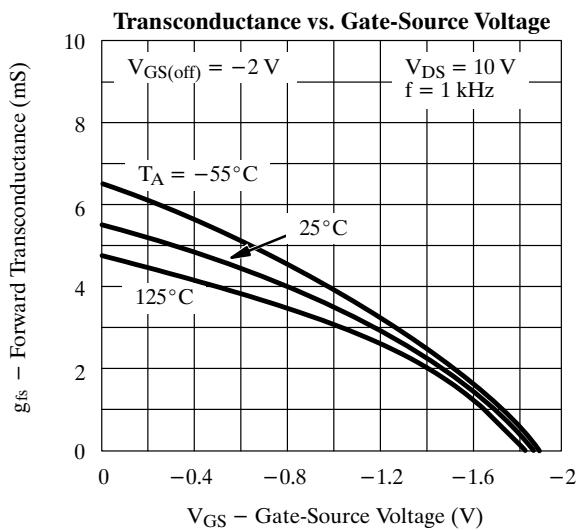
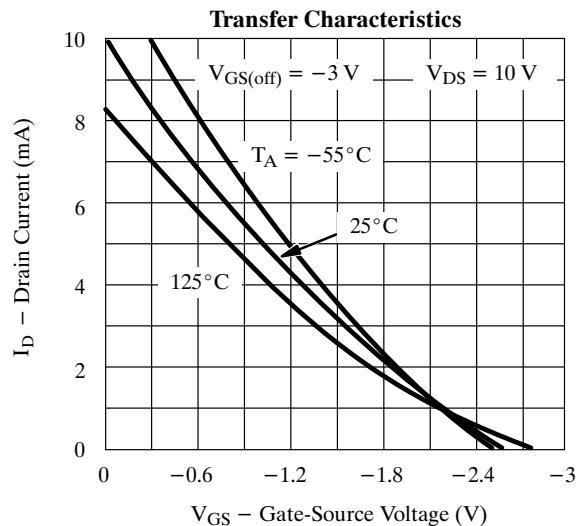
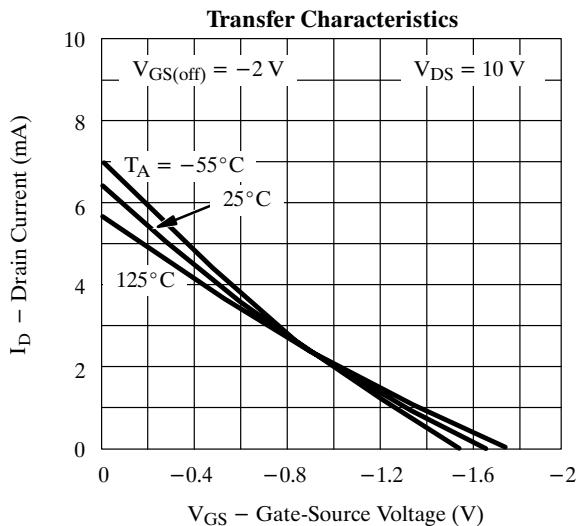
- a. T_A = 25°C unless otherwise noted.
- b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- c. Pulse test: PW ≤ 300 μs, duty cycle ≤ 2%.

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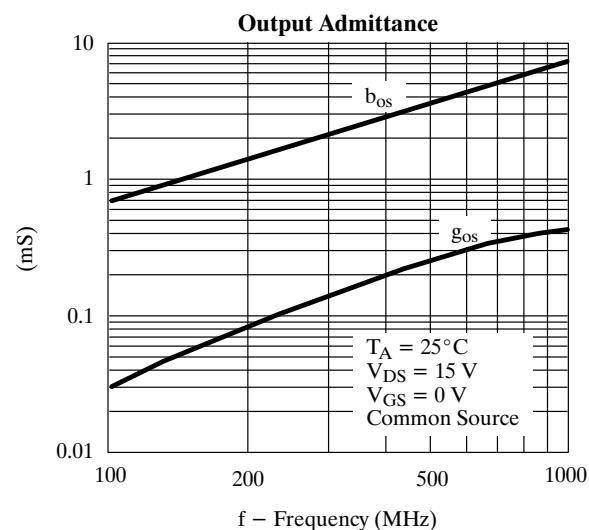
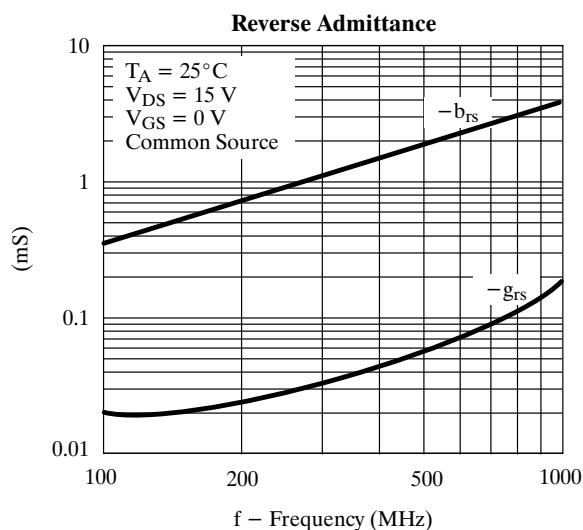
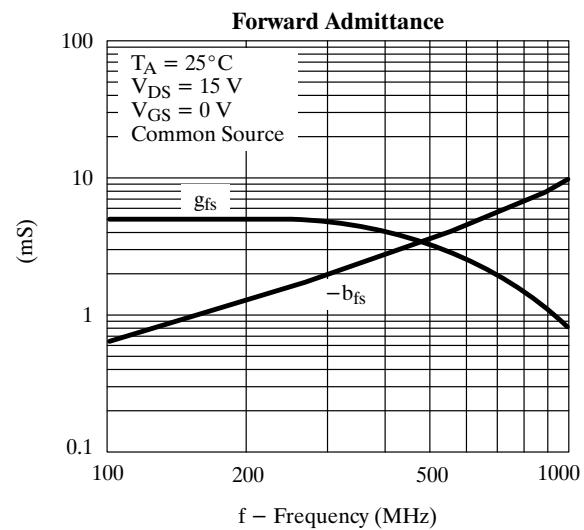
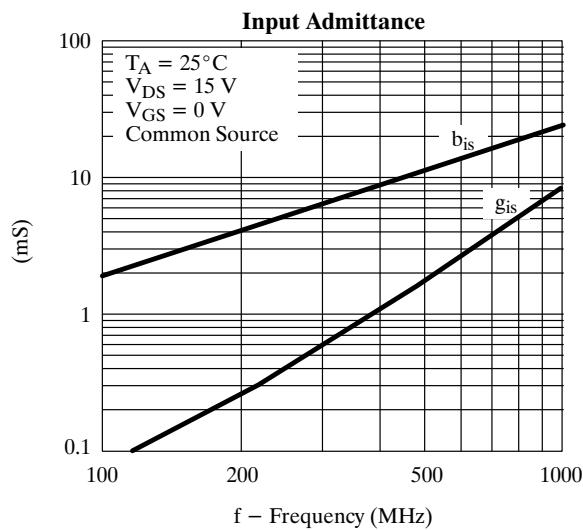
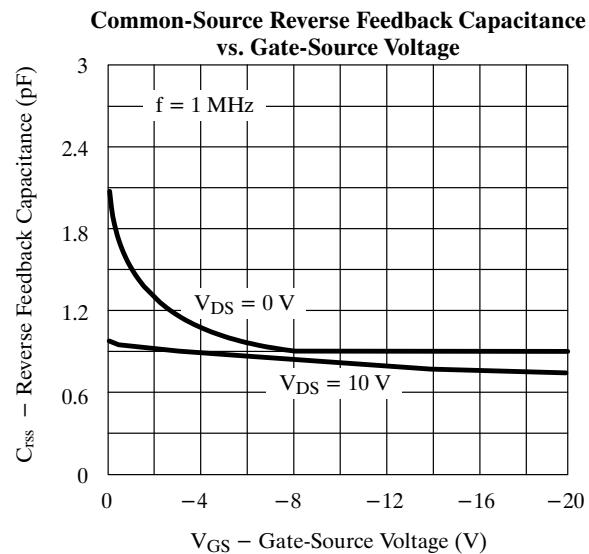
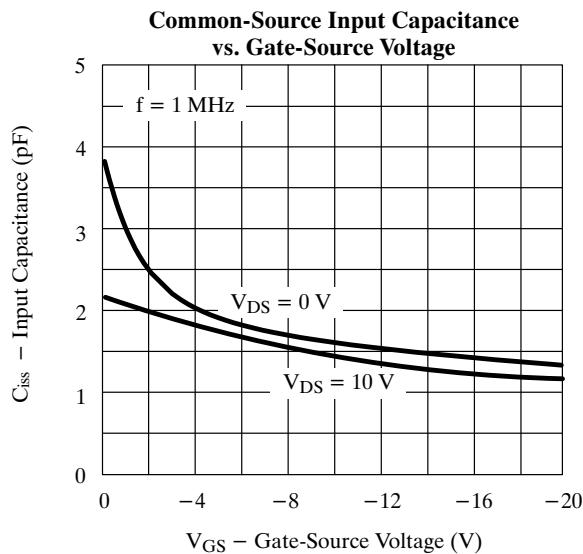
Typical Characteristics



Typical Characteristics (Cont'd)



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Typical Characteristics (Cont'd)

